

Amendments to the Claims:

Claims 1-18. (Previously canceled).

19. (Currently Amended) A method of fabricating a transistor source/drain contact between adjacent transistor gate structures comprising:

depositing an amorphous carbon filler material at least in a region between the adjacent transistor gate structures;

~~planarizing~~ planarizing the amorphous carbon filler material such that the planarized amorphous carbon filler material is a continuous layer that remains only between the adjacent transistor gate structures;

removing the planarized amorphous carbon filler material with a process having a removal selectivity to nitride greater than 40:1 to form a contact opening; and

depositing a conductive material in the contact opening.

20. (Currently Amended) A method of fabricating a transistor source/drain contact between adjacent transistor gate structures having nitride sidewall spacers comprising:

depositing an amorphous carbon filler material at least in a region between the adjacent transistor gate structures;

~~planarizing~~ planarizing the amorphous carbon filler material such that the planarized amorphous carbon filler material is a continuous layer that remains only between the adjacent transistor gate structures;

removing the planarized filler material with a process having a removal selectivity to nitride greater than 40:1 to form a contact opening having an aspect ratio greater than about 5:1; and

depositing a conductive material in the contact opening.

21. (Currently Amended) A method of fabricating a transistor source/drain connection between adjacent transistor gate structures comprising:

depositing an amorphous carbon filler material at least in a region between the adjacent transistor gate structures;

planarizing the amorphous carbon filler material such that the planarized amorphous carbon filler material is a continuous layer that remains only between the adjacent transistor gate structures;

selectively dry developing the planarized amorphous carbon filler material in the region between the adjacent transistor gate structures to form a contact opening; and

depositing a polysilicon material in the contact opening.

Please cancel claims 22 – 33.

Claims 22 – 33. (Currently canceled).